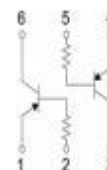
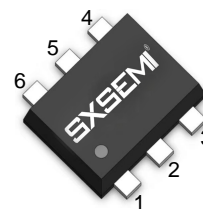


FEATURES

- | Two DTA143T chips in a package
- | Transistor elements are independent, eliminating interference
- | Mounting cost and area can be cut in half

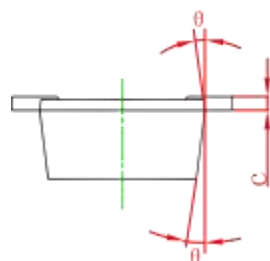
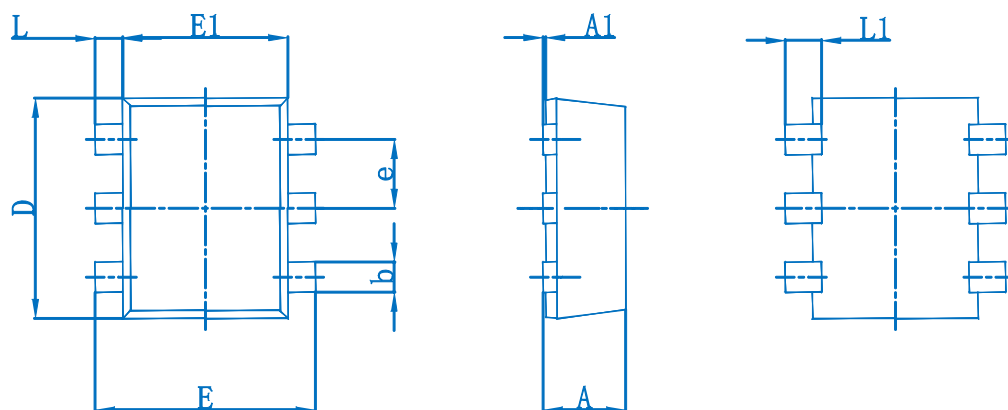
SOT-563
MARKING: B3

Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{(BR)CBO}$	-50	V
Collector-emitter voltage	$V_{(BR)CEO}$	-50	V
Emitter-base voltage	$V_{(BR)EBO}$	-5	V
Collector current	I_C	-100	mA
Collector Power dissipation	P_C	150	mW
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

Electrical characteristics (Ta=25°C)

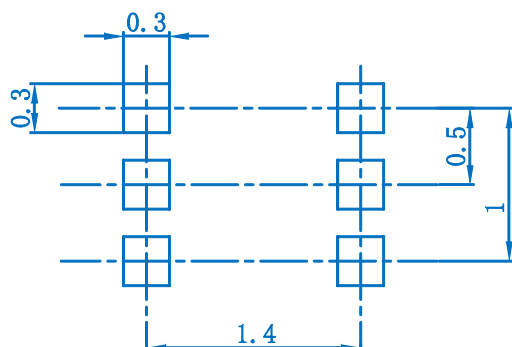
Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	-50			V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-50			V	$I_C = -1mA$
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-5			V	$I_E = -50\mu A$
Collector cut-off current	I_{CBO}			-0.5	μA	$V_{CB} = -50V$
Emitter cut-off current	I_{EBO}			-0.5	μA	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$			-0.3	V	$I_C = -5mA, I_B = -2.5mA$
DC current transfer ratio	h_{FE}	100		600		$V_{CE} = -5V, I_C = -1mA$
Input resistance	R_1	3.29	4.7	6.11	K Ω	
Transition frequency	f_T		250		MHZ	$V_{CE} = 10V, I_E = -5mA, f = 100MHZ$

SOT-563 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	10° REF.		10° REF.	

SOT-563 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.